

32001 U.S. PTO
10/015847
12/10/01

PATENT NUMBER and
ISSUE DATE

U.S. UTILITY Patent Application

APPL NUM 10015847	FILING DATE 12/10/2001	CLASS 257	SUBCLASS 3651	GAU 284	EXAMINER Lew. IS
**APPLICANTS: Letavic Theodore; Simpson Mark; 2822					
**CONTINUING DATA VERIFIED:					
** FOREIGN APPLICATIONS VERIFIED:					
PUBLISHED <input type="checkbox"/>			RESCIND <input type="checkbox"/>		
Priority claimed <input type="checkbox"/> yes <input type="checkbox"/> no			ATTORNEY DOCKET NO		
US PTO 110 conditions met <input type="checkbox"/> yes <input type="checkbox"/> no			US 010610		
Verifying Acknowledged Applicant's Initials					
TITLE: Dual gate oxide high-voltage semiconductor device and method for forming the same					
U.S. DEPT. OF COMM./PAT. & TM-PTO-436L (Rev. 12-94)					

NOTICE OF ALLOWANCE MAILED		CLAIMS ALLOWED	
		Assistant Examiner	Total Claims
			Print Claim for O.G.
ISSUE FEE			DRAWING
Amount Due	Date Paid		Sheets Drawg. Figs. Drawg. Print Fig.
		Primary Examiner	
<input type="checkbox"/> TERMINAL DISCLAIMER		PREPARED FOR ISSUE	Application Examiner
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